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BY: _____
11 NOV 18 PM 1:33
CLERK U.S. DISTRICT COURT
CENTRAL DIST. OF CALIF.
LOS ANGELES

FILED

8 Attorney for Plaintiff,

9 **SEMICONDUCTOR TECHNOLOGIES LLC**

10 UNITED STATES DISTRICT COURT
11 CENTRAL DISTRICT OF CALIFORNIA

12 SEMICONDUCTOR TECHNOLOGIES
13 LLC,

14 Plaintiff,

15 vs.

16 HYNIX SEMICONDUCTOR
17 AMERICA INC.;
18 HYNIX SEMICONDUCTOR
19 MANUFACTURING AMERICA INC.;
20 AND
21 HYNIX SEMICONDUCTOR INC.;

22 Defendants.

Case No.: _____

SACV11-1788 JSI (RNPK)

**ORIGINAL COMPLAINT FOR
PATENT INFRINGEMENT**

JURY TRIAL DEMANDED

Filing Date: TBD

Trial Date: TBD

Discovery Cut-off: TBD

Motion Cut-off: TBD

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24 This is an action for patent infringement in which Semiconductor Technologies
25 LLC submits this Original Complaint against Hynix Semiconductor America Inc.;
26 Hynix Semiconductor Manufacturing America Inc.; and Hynix Semiconductor Inc.
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1 7. STL is the exclusive licensee of United States Patent No. 6,828,242
2 (“the ‘242 patent”), entitled “Method for Manufacturing Semiconductor Integrated
3 Circuit Device.” The ‘242 patent was duly and legally issued on December 7, 2004.
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5 8. As exclusive licensee, STL holds all substantial rights in and to
6 the ‘242 patent, including, without limitation, the exclusive right to grant sublicenses,
7 to sue for and collect past, present and future damages, and the exclusive right to seek
8 and obtain injunctive relief or any other relief for infringement of the ‘242 patent.
9 Accordingly, STL has standing to bring this lawsuit for infringement of the ‘242
10 patent.
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13 9. On information and belief, Hynix has infringed the ‘242 patent by actions
14 comprising making and using the methods claimed in the ‘242 patent in the
15 manufacture of semiconductor integrated circuit devices, including DRAM chips such
16 as the Hynix H5TQ1G83BFR 54nm 1G DDR3 SDRAM and similar chips, including
17 practicing the steps of (a) forming a silicon film over a semiconductor substrate via a
18 first insulating film; (b) forming a refractory metal film on the silicon film; (c)
19 forming a second insulating film on the refractory metal film; (d) processing the
20 second insulating film into a predetermined shape; (e) etching the refractory metal
21 film and a predetermined thickness of a part of the silicon film where it is not covered
22 with the predetermined shaped second insulating film so as not to expose the first
23 insulating film; (f) selectively forming a third insulating film on a sidewall of the
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1 13. As exclusive licensee, STL holds all substantial rights in and to
2 the '034 patent, including, without limitation, the exclusive right to grant sublicenses,
3 to sue for and collect past, present and future damages, and the exclusive right to seek
4 and obtain injunctive relief or any other relief for infringement of the '034 patent.
5 Accordingly, STL has standing to bring this lawsuit for infringement of
6 the '034 patent.
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9 14. On information and belief, Hynix has been and now is infringing
10 the '034 patent by actions comprising making, using, selling, offering for sale and/or
11 importing semiconductor integrated circuit devices, including DRAM chips such as
12 the Hynix H5TQ1G83BFR 54nm 1G DDR3 SDRAM and similar chips, that comprise
13 (a) a semiconductor substrate having a main surface; (b) a first insulating film formed
14 on the main surface of the semiconductor substrate; (c) a silicon film formed on the
15 first insulating film, which has a first sidewall positioned adjacent to the first
16 insulating film and a second sidewall positioned apart from the first insulating film;
17 (d) a refractory metal film formed above the silicon film and having a third sidewall;
18 (e) a second insulating film formed on the second and third sidewalls; and (f) a third
19 insulating film formed on the first sidewall, wherein the third insulating film has a
20 first portion positioned between the first and second insulating films and a second
21 portion positioned between the first portion and the silicon film, wherein an upper end
22 of the second portion of the third insulating film is higher than that of the first portion
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